Marubeni

SPECIFICATION OF INFRARED LED CHIP

CN870-35P

[INFRARED]

1) Commodity Type and Physical Characteristics.

1. Material		GaAlAs/GaAlAs(DDH)	
2. Electrode	Top Side	P (anode) side	: Au Alloy
	Bottom Side	N (cathode) side	: Au Alloy
3. Electrode Pattern			Fig.1
4. Chip Size			Fig.2
5. Chip Thickness			Fig.2
6. Emission Area			Fig.2

2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.45	1.7	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	3.0	4.5		mW
Peak Wavelength	λP	If=20mA	860	870	880	nm
Spectral Radiation Bandwidth	Δλ	If=20mA		40		nm
Rise Time	tr	If=20mA		15		ns
Full time	tf	If=20mA		10		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um

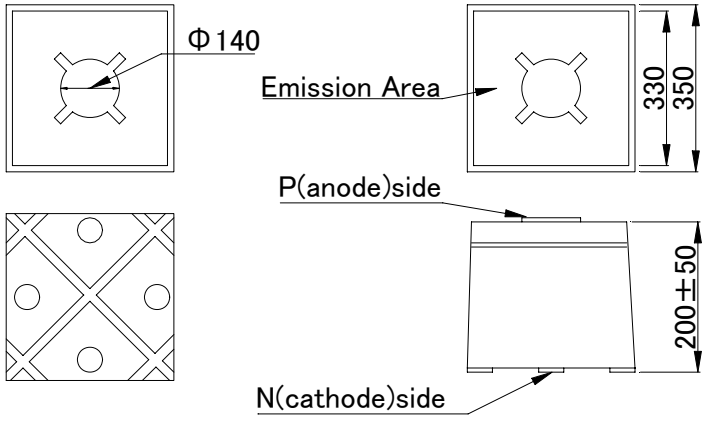

Fig.1 Electrode Pattern Fig.2 Chip size and Emission Area

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